## M Pepper

# List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

611 23,189 64 137 h-index g-index citations papers 618 24,810 6.15 3.3 avg, IF L-index ext. citations ext. papers

#	Paper	IF	Citations
611	Advances in interaction effects in the quasi one-dimensional electron gas. <i>Frontiers of Nanoscience</i> , <b>2021</b> , 20, 7-29	0.7	
610	Single-electron pump with highly controllable plateaus. <i>Applied Physics Letters</i> , <b>2021</b> , 119, 153102	3.4	
609	Engineering electron wavefunctions in asymmetrically confined quasi one-dimensional structures. <i>Applied Physics Letters</i> , <b>2021</b> , 118, 124002	3.4	1
608	Interactions and non-magnetic fractional quantization in one-dimension <i>Applied Physics Letters</i> , <b>2021</b> , 119, 110502	3.4	0
607	Activated and Metallic Conduction in p-Type Modulation-Doped Ge-Sn Devices. <i>Physical Review Applied</i> , <b>2020</b> , 14,	4.3	2
606	Zero-Magnetic Field Fractional Quantum States. <i>Physical Review Letters</i> , <b>2019</b> , 122, 086803	7.4	10
605	Formation of a non-magnetic, odd-denominator fractional quantized conductance in a quasi-one-dimensional electron system. <i>Applied Physics Letters</i> , <b>2019</b> , 115, 123104	3.4	3
604	Conductance quantisation in patterned gate InGaAs structures up to 6 \( \preceq (2e /h)\). <i>Journal of Physics Condensed Matter</i> , <b>2019</b> , 31, 104002	1.8	
603	Cavity assisted spin reconfiguration in a quantum wire. <i>Journal of Physics: Conference Series</i> , <b>2018</b> , 964, 012003	0.3	
602	Self-organised fractional quantisation in a hole quantum wire. <i>Journal of Physics Condensed Matter</i> , <b>2018</b> , 30, 09LT01	1.8	13
601	Engineering the spin polarization of one-dimensional electrons. <i>Journal of Physics Condensed Matter</i> , <b>2018</b> , 30, 08LT01	1.8	8
600	LO-Phonon Emission Rate of Hot Electrons from an On-Demand Single-Electron Source in a GaAs/AlGaAs Heterostructure. <i>Physical Review Letters</i> , <b>2018</b> , 121, 137703	7.4	14
599	Direct observation of spin polarization in GaAs quantum wires by transverse electron focusing. Journal of Physics: Conference Series, 2018, 964, 012002	0.3	2
598	Ultrafast voltage sampling using single-electron wavepackets. <i>Applied Physics Letters</i> , <b>2017</b> , 110, 10210	53.4	19
597	Controlled spatial separation of spins and coherent dynamics in spin-orbit-coupled nanostructures. <i>Nature Communications</i> , <b>2017</b> , 8, 15997	17.4	15
596	Tunneling of hybridized pairs of electrons through a one-dimensional channel. <i>Advances in Physics: X</i> , <b>2017</b> , 2, 545-568	5.1	1
595	Quantum ballistic transport in strained epitaxial germanium. <i>Applied Physics Letters</i> , <b>2017</b> , 111, 233512	3.4	8

### (2010-2016)

594	Time-of-Flight Measurements of Single-Electron Wave Packets in Quantum Hall Edge States. <i>Physical Review Letters</i> , <b>2016</b> , 116, 126803	7.4	44
593	Early work on semiconductor quantum nanoelectronics in the Cavendish Laboratory. <i>Journal of Physics Condensed Matter</i> , <b>2016</b> , 28, 421003	1.8	1
592	Non-invasive charge detection in surface-acoustic-wave-defined dynamic quantum dots. <i>Applied Physics Letters</i> , <b>2016</b> , 109, 183501	3.4	
591	All-electric all-semiconductor spin field-effect transistors. <i>Nature Nanotechnology</i> , <b>2015</b> , 10, 35-9	28.7	206
590	Noncollinear paramagnetism of a GaAs two-dimensional hole system. <i>Physical Review Letters</i> , <b>2014</b> , 113, 236401	7.4	8
589	Evidence of Novel Quasiparticles in a Strongly Interacting Two-Dimensional Electron System: Giant Thermopower and Metallic Behaviour. <i>Journal of Low Temperature Physics</i> , <b>2013</b> , 171, 626-631	1.3	8
588	Application of terahertz pulsed imaging to analyse film coating characteristics of sustained-release coated pellets. <i>International Journal of Pharmaceutics</i> , <b>2013</b> , 457, 521-6	6.5	30
587	Magnetic focusing with quantum point contacts in the non-equilibrium transport regime. <i>Applied Physics Letters</i> , <b>2013</b> , 103, 093503	3.4	3
586	Clock-controlled emission of single-electron wave packets in a solid-state circuit. <i>Physical Review Letters</i> , <b>2013</b> , 111, 216807	7.4	88
585	Quantum conductance in silicon oxide resistive memory devices. <i>Scientific Reports</i> , <b>2013</b> , 3, 2708	4.9	126
584	All-electrical injection and detection of a spin-polarized current using 1D conductors. <i>Physical Review Letters</i> , <b>2012</b> , 109, 177202	7.4	22
583	Disorder and Interaction Effects in Quantum Wires. <i>Journal of Physics: Conference Series</i> , <b>2012</b> , 376, 012	20:1.8	8
582	Experimental Progress towards Probing the Ground State of an Electron-Hole Bilayer by Low-Temperature Transport. <i>Advances in Condensed Matter Physics</i> , <b>2011</b> , 2011, 1-22	1	17
581	Compressibility measurements of quasi-one-dimensional quantum wires. <i>Physical Review Letters</i> , <b>2011</b> , 107, 126801	7.4	10
580	Single- and few-electron dynamic quantum dots in a perpendicular magnetic field. <i>Journal of Applied Physics</i> , <b>2011</b> , 109, 102422	2.5	9
579	Disorder and electron interaction control in low-doped silicon metal-oxide-semiconductor field effect transistors. <i>Applied Physics Letters</i> , <b>2010</b> , 97, 142108	3.4	4
578	Electrons in one dimension. <i>Philosophical Transactions Series A, Mathematical, Physical, and Engineering Sciences</i> , <b>2010</b> , 368, 1141-62	3	29
577	Direct observation of nonequilibrium spin population in quasi-one-dimensional nanostructures. <i>Nano Letters</i> , <b>2010</b> , 10, 2330-4	11.5	11

576	An accurate high-speed single-electron quantum dot pump. <i>New Journal of Physics</i> , <b>2010</b> , 12, 073013	2.9	47
575	Coupled double-row formation in a quasi-1D wire. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , <b>2010</b> , 42, 1114-1117	3	4
574	Double-row transport in quantum wires of shallow confinement. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , <b>2010</b> , 42, 1118-1121	3	4
573	Towards the ground state of an electronBole bilayer. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , <b>2010</b> , 42, 1247-1250	3	5
572	Radio-frequency reflectometry fast and sensitive measurement method for two-dimensional systems. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , <b>2010</b> , 42, 1192-1195	3	1
571	Benefits of using undoped GaAs/AlGaAs heterostructures: A case study of the zero-bias bias anomaly in quantum wires. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , <b>2010</b> , 42, 1200-1204	4 <sup>3</sup>	8
570	Parallel quantized charge pumping. <i>Physical Review B</i> , <b>2009</b> , 80,	3.3	33
569	Row coupling in an interacting quasi-one-dimensional quantum wire investigated using transport measurements. <i>Physical Review B</i> , <b>2009</b> , 80,	3.3	35
568	Possible effect of collective modes in zero magnetic field transport in an electron-hole bilayer. <i>Physical Review B</i> , <b>2009</b> , 80,	3.3	14
567	Nuclear spin coherence in a quantum wire. <i>Physical Review B</i> , <b>2009</b> , 80,	3.3	13
566	Non-Kondo zero-bias anomaly in quantum wires. <i>Physical Review B</i> , <b>2009</b> , 79,	3.3	24
565	Odd-even spin effects and variation of g factor in a quasi-one-dimensional subband. <i>Physical Review B</i> , <b>2009</b> , 79,	3.3	13
564	Incipient formation of an electron lattice in a weakly confined quantum wire. <i>Physical Review Letters</i> , <b>2009</b> , 102, 056804	7.4	63
563	Molecular beam epitaxy of high mobility In0.75Ga0.25As for electron spin transport applications. Journal of Vacuum Science & Technology B, <b>2009</b> , 27, 2066		4
562	Spin-split excitation gap and spin entanglement of a pair of interacting electrons in a quantum dot. <i>Semiconductor Science and Technology</i> , <b>2009</b> , 24, 115001	1.8	5
561	MBE growth and patterned backgating of electronfiole bilayer structures. <i>Journal of Crystal Growth</i> , <b>2009</b> , 311, 1988-1993	1.6	2
560	Terahertz pulsed imaging as an analytical tool for sustained-release tablet film coating. European		-6
	Journal of Pharmaceutics and Biopharmaceutics, <b>2009</b> , 71, 117-23	5.7	56

558	Zero-bias anomaly in quantum wires. <i>Physical Review B</i> , <b>2009</b> , 79,	3.3	38
557	Coherent time evolution of a single-electron wave function. <i>Physical Review Letters</i> , <b>2009</b> , 102, 156801	7.4	52
556	Characterisation of spin-incoherent transport in one dimension. <i>Journal of Physics: Conference Series</i> , <b>2009</b> , 150, 032029	0.3	
555	Impact of long- and short-range disorder on the metallic behaviour of two-dimensional systems.  Nature Physics, 2008, 4, 55-59	16.2	35
554	Bychkov <b>R</b> ashba dominated band structure in an In0.75Ga0.25As <b>I</b> h0.75Al0.25As device with spin-split carrier densities of . <i>Journal of Physics Condensed Matter</i> , <b>2008</b> , 20, 472207	1.8	9
553	Bias-controlled spin polarization in quantum wires. <i>Applied Physics Letters</i> , <b>2008</b> , 93, 032102	3.4	40
552	Spin-incoherent transport in quantum wires. <i>Physical Review Letters</i> , <b>2008</b> , 101, 036801	7.4	42
551	The 0.7 anomaly in one-dimensional hole quantum wires. <i>Journal of Physics Condensed Matter</i> , <b>2008</b> , 20, 164205	1.8	8
550	Variation of the hopping exponent in disordered silicon MOSFETs. <i>Journal of Physics Condensed Matter</i> , <b>2008</b> , 20, 415226	1.8	1
549	Spin effects in one-dimensional systems. <i>Journal of Physics Condensed Matter</i> , <b>2008</b> , 20, 164213	1.8	7
548	Effect of screening long-range Coulomb interactions on the metallic behavior in two-dimensional hole systems. <i>Physical Review B</i> , <b>2008</b> , 77,	3.3	14
547	Magnetic-field-induced instabilities in localized two-dimensional electron systems. <i>Physical Review B</i> , <b>2008</b> , 78,	3.3	1
546	Spin injection from Co2MnGa into an InGaAs quantum well. <i>Applied Physics Letters</i> , <b>2008</b> , 92, 232101	3.4	20
545	Patterned backgating using single-sided mask aligners: Application to density-matched electron-hole bilayers. <i>Journal of Applied Physics</i> , <b>2008</b> , 104, 113715	2.5	6
544	Radio-frequency reflectometry on large gated two-dimensional systems. <i>Review of Scientific Instruments</i> , <b>2008</b> , 79, 123901	1.7	10
543	Quantum transport in In0.75Ga0.25As quantum wires. <i>Applied Physics Letters</i> , <b>2008</b> , 92, 152108	3.4	23
542	Elimination of scattering effects in spectral measurement of granulated materials using terahertz pulsed spectroscopy. <i>Applied Physics Letters</i> , <b>2008</b> , 92, 051103	3.4	82
541	0.7 Structure and zero bias anomaly in ballistic hole quantum wires. <i>Physical Review Letters</i> , <b>2008</b> , 100, 016403	7.4	26

540	Field-induced modulation of the conductance, thermoelectric power, and magnetization in ballistic coupled double quantum wires under a tilted magnetic field. <i>Physical Review B</i> , <b>2008</b> , 77,	3.3	18
539	Anticrossing of spin-split subbands in quasi-one-dimensional wires. <i>Physical Review Letters</i> , <b>2008</b> , 100, 226804	7.4	2
538	Kondo effect from a tunable bound state within a quantum wire. <i>Physical Review Letters</i> , <b>2008</b> , 100, 02	6807	54
537	Enhanced current quantization in high-frequency electron pumps in a perpendicular magnetic field. <i>Physical Review B</i> , <b>2008</b> , 78,	3.3	41
536	Anomalous coulomb drag in electron-hole bilayers. <i>Physical Review Letters</i> , <b>2008</b> , 101, 246801	7.4	88
535	Quantum transport in one-dimensional GaAs hole systems. <i>International Journal of Nanotechnology</i> , <b>2008</b> , 5, 318	1.5	1
534	Effects of inelastic capture, tunneling escape, and quantum confinement on surface acoustic wave-dragged photocurrents in quantum wells. <i>Journal of Applied Physics</i> , <b>2008</b> , 103, 083714	2.5	4
533	Measurement of Coulomb-energy-dependent tunnelling rates in surface-acoustic-wave-defined dynamic quantum dots. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , <b>2008</b> , 40, 1136-1138	3	8
532	Spontaneous spin polarisation in one dimension under finite DC-bias. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , <b>2008</b> , 40, 1295-1297	3	1
531	Investigation of single-electron dynamics in tunnelling between zero- and one-dimensional states. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , <b>2008</b> , 40, 1017-1021	3	3
530	Field-tunable magnetic phases in a semiconductor-based two-dimensional Kondo lattice. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , <b>2008</b> , 40, 942-948	3	1
529	Sensitivity of the magnetic state of a spin lattice on itinerant electron orbital phase. <i>Physica E:</i> Low-Dimensional Systems and Nanostructures, <b>2008</b> , 40, 1460-1463	3	1
528	0.7 Structure and zero bias anomaly in one-dimensional hole systems. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , <b>2008</b> , 40, 1501-1503	3	
527	Electron population control of a highly isolated quantum dot using surface-acoustic waves. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , <b>2008</b> , 40, 1596-1598	3	1
526	Metallic behavior in low-disorder two-dimensional hole systems in the presence of long- and short-range disorder. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , <b>2008</b> , 40, 1599-1601	3	
525	Screening long-range Coulomb interactions in 2D hole systems using a bilayer heterostructure. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , <b>2008</b> , 40, 1700-1702	3	1
524	Tuning the confinement strength in a split-gate quantum wire. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , <b>2008</b> , 40, 1645-1647	3	7
523	Selective breakdown of quantum Hall edge states and non-monotonic Coulomb drag in a GaAsAlGaAs electronfiole bilayer. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , <b>2008</b> , 40, 1693-1696	3	10

### (2006-2008)

522	Electron pumping through quantum dots defined in parallel etched quantum wires. <i>Microelectronics Journal</i> , <b>2008</b> , 39, 365-368	1.8	2
521	Energy-dependent tunneling from few-electron dynamic quantum dots. <i>Physical Review Letters</i> , <b>2007</b> , 99, 156802	7.4	41
520	Drug hydrate systems and dehydration processes studied by terahertz pulsed spectroscopy. <i>International Journal of Pharmaceutics</i> , <b>2007</b> , 334, 78-84	6.5	111
519	Magnetoconductivity of Hubbard bands induced in silicon MOSFETs. <i>Physica B: Condensed Matter</i> , <b>2007</b> , 400, 218-223	2.8	2
518	Comparison of vibrational spectroscopy techniques to investigate the dehydration behaviour of piroxicam monohydrate from compacts. <i>European Journal of Pharmaceutical Sciences</i> , <b>2007</b> , 32, S9	5.1	
517	Analysis of sustained-release tablet film coats using terahertz pulsed imaging. <i>Journal of Controlled Release</i> , <b>2007</b> , 119, 253-61	11.7	127
516	Activation mechanisms in sodium-doped silicon MOSFETs. <i>Journal of Physics Condensed Matter</i> , <b>2007</b> , 19, 226216	1.8	5
515	Suppression of spin-splitting in Al0.33Ga0.67As/AlyGa1¶As heterostructures withyvarying from 0.10 to 0.15. <i>Semiconductor Science and Technology</i> , <b>2007</b> , 22, 722-727	1.8	1
514	Strongly bias-dependent spin injection from Fe into n-type GaAs. <i>Physical Review B</i> , <b>2007</b> , 75,	3.3	9
513	Collapse of nonequilibrium charge states in an isolated quantum dot using surface acoustic waves. <i>Physical Review B</i> , <b>2007</b> , 75,	3.3	4
512	Energy-level pinning and the 0.7 spin state in one dimension: GaAs quantum wires studied using finite-bias spectroscopy. <i>Physical Review B</i> , <b>2007</b> , 75,	3.3	32
511	Single-electron population and depopulation of an isolated quantum dot using a surface-acoustic-wave pulse. <i>Physical Review Letters</i> , <b>2007</b> , 98, 046801	7.4	33
510	Gigahertz quantized charge pumping. <i>Nature Physics</i> , <b>2007</b> , 3, 343-347	16.2	308
509	Conductance quantization at a half-integer plateau in a symmetric GaAs quantum wire. <i>Science</i> , <b>2006</b> , 312, 1359-62	33.3	78
508	Gating schemes for controlling the electron wavefunction between GaAs and In0.05Ga0.95As quasi-one-dimensional channels. <i>Journal of Physics Condensed Matter</i> , <b>2006</b> , 18, L123-L128	1.8	6
507	Zeeman splitting in ballistic hole quantum wires. <i>Physical Review Letters</i> , <b>2006</b> , 97, 026403	7.4	75
506	Evidence for multiple impurity bands in sodium-doped silicon MOSFETs. <i>Physical Review B</i> , <b>2006</b> , 73,	3.3	8
505	Examination of multiply reflected surface acoustic waves by observing acoustoelectric current generation under pulse modulation. <i>Physical Review B</i> , <b>2006</b> , 74,	3.3	7

504	Examination of surface acoustic wave reflections by observing acoustoelectric current generation under pulse modulation. <i>Applied Physics Letters</i> , <b>2006</b> , 89, 132102	3.4	12
503	Conductance quantization and the 0.7De2E conductance anomaly in one-dimensional hole systems. <i>Applied Physics Letters</i> , <b>2006</b> , 88, 012107	3.4	37
502	Experimental investigation of the surface acoustic wave electron capture mechanism. <i>Physical Review B</i> , <b>2006</b> , 74,	3.3	30
501	Fano effect and Kondo effect in quantum dots formed in strongly coupled quantum wells. <i>Physical Review B</i> , <b>2006</b> , 73,	3.3	12
500	Quantum-dot thermometry of electron heating by surface acoustic waves. <i>Applied Physics Letters</i> , <b>2006</b> , 89, 122104	3.4	25
499	The effect of pulse-modulated surface acoustic waves on acoustoelectric current quantization. <i>Journal of Applied Physics</i> , <b>2006</b> , 100, 063710	2.5	21
498	Ballistic electron spectroscopy. <i>Applied Physics Letters</i> , <b>2006</b> , 89, 212103	3.4	5
497	Single-electron transfer between double quantum dots defined by surface acoustic waves. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , <b>2006</b> , 34, 546-549	3	6
496	Closely spaced, independently contacted electronfiole bilayers in GaAsAlGaAs heterostructures. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , <b>2006</b> , 34, 689-692	3	
495	Ballistic transport in one-dimensional bilayer hole systems. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , <b>2006</b> , 34, 550-552	3	2
494	New interaction effects in quantum point contacts at high magnetic fields. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , <b>2006</b> , 34, 588-591	3	6
493	Continuous-wave terahertz system with a 60 dB dynamic range. <i>Applied Physics Letters</i> , <b>2005</b> , 86, 20410	043.4	75
492	Fabrication of closely spaced, independently contacted electron-hole bilayers in GaAs-AlGaAs heterostructures. <i>Applied Physics Letters</i> , <b>2005</b> , 87, 202104	3.4	20
491	Terahertz Frequency Sensing and Imaging: A Time of Reckoning Future Applications?. <i>Proceedings of the IEEE</i> , <b>2005</b> , 93, 1722-1743	14.3	278
490	Evidence for a finite compressibility of a quasi-one-dimensional ballistic channel. <i>Microelectronics Journal</i> , <b>2005</b> , 36, 331-333	1.8	
489	Single-photon detection mechanism in a quantum dot transistor. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , <b>2005</b> , 26, 356-360	3	2
488	Jain Livelson-type resonance as a noninvasive probe of screening in the quantum Hall regime. <i>Microelectronics Journal</i> , <b>2005</b> , 36, 425-427	1.8	1
487	Interaction effects in high-mobility two-dimensional electron and hole systems. <i>Physica Status Solidi</i> (B): Basic Research, <b>2005</b> , 242, 1204-1208	1.3	1

#### (2004-2005)

486	Chemical mapping using reflection terahertz pulsed imaging. <i>Semiconductor Science and Technology</i> , <b>2005</b> , 20, S254-S257	1.8	44
485	Spin injection between epitaxial Co2.4Mn1.6Ga and an InGaAs quantum well. <i>Applied Physics Letters</i> , <b>2005</b> , 86, 252106	3.4	44
484	Interaction correction to the longitudinal conductivity and Hall resistivity in high-quality two-dimensional GaAs electron and hole systems. <i>Physical Review B</i> , <b>2005</b> , 72,	3.3	10
483	Acoustoelectric current transport through a double quantum dot. <i>Physical Review B</i> , <b>2005</b> , 72,	3.3	13
482	Local transport in a disorder-stabilized correlated insulating phase. <i>Physical Review B</i> , <b>2005</b> , 72,	3.3	18
481	Evolution of the bilayer ⊞1 quantum Hall state under charge imbalance. <i>Physical Review B</i> , <b>2005</b> , 71,	3.3	14
480	Acoustoelectric current in submicron-separated quantum wires. Applied Physics Letters, 2005, 86, 1521	053.4	12
479	Zero-bias anomaly and kondo-assisted quasiballistic 2D transport. <i>Physical Review Letters</i> , <b>2005</b> , 95, 06	66603	11
478	Anomalous spin-dependent behavior of one-dimensional subbands. <i>Physical Review B</i> , <b>2005</b> , 72,	3.3	15
477	Measurements of composite fermion conductivity dependence on carrier density. <i>Journal of Physics Condensed Matter</i> , <b>2004</b> , 16, 1095-1101	1.8	1
476	Unusual conductance collapse in one-dimensional quantum structures. <i>Journal of Physics Condensed Matter</i> , <b>2004</b> , 16, L279-L286	1.8	7
475	Gradual decrease of conductance of an adiabatic ballistic constriction below 2e2fi. <i>Physical Review B</i> , <b>2004</b> , 70,	3.3	8
474	Noninvasive detection of the evolution of the charge states of a double dot system. <i>Physical Review B</i> , <b>2004</b> , 69,	3.3	15
473	Masking by weak localization of metallic behavior in a two-dimensional electron system in strong parallel magnetic fields. <i>Physical Review B</i> , <b>2004</b> , 69,	3.3	6
472	Dynamic localization of two-dimensional electrons at mesoscopic length scales. <i>Physical Review B</i> , <b>2004</b> , 70,	3.3	12
471	Quantized charge pumping through a quantum dot by surface acoustic waves. <i>Applied Physics Letters</i> , <b>2004</b> , 84, 4319-4321	3.4	51
470	Weak localization in high-quality two-dimensional systems. <i>Physical Review B</i> , <b>2004</b> , 70,	3.3	46
469	Noninvasive lateral detection of Coulomb blockade in a quantum dot fabricated using atomic force microscopy. <i>Journal of Applied Physics</i> , <b>2004</b> , 95, 2557-2559	2.5	12

468	Stability of the bilayer   1 quantum Hall state under charge imbalance. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , <b>2004</b> , 22, 40-43	3	1
467	Can the conductance step of a single-mode ballistic constriction be lower than 2e2/h?. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , <b>2004</b> , 22, 268-271	3	
466	0.7 Analogue structures and exchange interactions in quantum wires. <i>Solid State Communications</i> , <b>2004</b> , 131, 591-597	1.6	9
465	Leakage current induced anomalies in the photoluminescence of GaAs coupled quantum wells. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2004</b> , 1, 612-615		
464	Interactions in high-mobility 2D electron and hole systems. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , <b>2004</b> , 22, 218-223	3	4
463	0.7 Structure in quantum wires observed at crossings of spin-polarised 1D subbands. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , <b>2004</b> , 22, 264-267	3	7
462	Non-invasive detection of the ionic and covalent charge states of an isolated double dot system. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , <b>2004</b> , 22, 522-525	3	2
461	Experimental evidence for screening effects from surface states in GaAs/AlGaAs based nanostructures. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , <b>2004</b> , 22, 570-573	3	3
460	Photon-induced conductance steps and in situ modulation of disorder in mesoscopic electron systems. <i>Physical Review B</i> , <b>2004</b> , 70,	3.3	4
459	Fano factor reduction on the 0.7 conductance structure of a ballistic one-dimensional wire. <i>Physical Review Letters</i> , <b>2004</b> , 93, 116602	7.4	72
458	Possible evidence of a spontaneous spin polarization in mesoscopic two-dimensional electron systems. <i>Physical Review Letters</i> , <b>2004</b> , 92, 116601	7.4	46
457	Influence of the thiol position on the attachment and subsequent hybridization of thiolated DNA on gold surfaces. <i>Langmuir</i> , <b>2004</b> , 20, 1527-30	4	15
456	Simulation of terahertz pulse propagation in biological systems. <i>Applied Physics Letters</i> , <b>2004</b> , 84, 2190-	-231.942	141
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	Evolution of GaAs quantum well excitons with excess electron density and magnetic field.	, ,	
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